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Mar 6, 2001

PUB-NO: JP02001059191A

DOCUMENT-IDENTIFIER: JP 2001059191 A

TITLE: ETCHING AGENT, PRODUCTION OF SUBSTRATE FOR ELECTRONIC EQUIPMENT USING THE SAME AND ELECTRONIC EQUIPMENT

PUBN-DATE: March 6, 2001

## INVENTOR-INFORMATION:

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APPL-NO: JP20000001127

APPL-DATE: January 6, 2000

INT-CL (IPC): C23F 1/18; C09K 13/00; C09K 13/06; H01L 21/308; H01L 21/3205; H01L 29/786; H01L 21/336

## ABSTRACT:

PROBLEM TO BE SOLVED: To provide an etching agent capable of etching a Cu film by an easy chemical etching method being a dipping method by rest process in the case that a Cu film of low resistance is used as a wiring material, small in the secular change of the etching grade and capable of preventing the occurrence of a pattern thinning phenomenon caused by the dispersion of the side etching amount of the Cu film.

SOLUTION: This etching agent consists of an aq. soln. contg. potassium peroxymonosulfate monohydrogen and hydrofluoric acid. In this method for producing a thin film transistor substrate, on the surface of a laminated film obtd. by successively laminating a Ti film or a Ti alloy 3 and a Cu film 4 on a substrate 2, masks 27 and 28 of prescribed patterns are formed, the laminated film is subjected to etching by using the etching agent having the compsn., and a gate electrode 5 (laminated wiring) 5 and a lower pad layer (laminated wiring) 16b of the prescribed patterns are formed.

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**BEST AVAILABLE COPY****Term:**

19 and (peroxosulfate)

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USPT,PGPB,JPAB,EPAB,DWPI,TDBD	I9 and (peroxosulfate)	1	<u>L11</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	I9 and (peroxosulfate)	1	<u>L10</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	I6 same (acetic acid)	949	<u>L9</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	I6 same (potassium near hydrogen near peroxomonosulfate or "KH S.sub.5" or "NaH S.sub.5")	0	<u>L8</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	I6 same (peroxomonosulfate)	1	<u>L7</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	copper same (etch\$3 or remov\$3 or polish\$3)	70589	<u>L6</u>
JPAB	11-173431	0	<u>L5</u>
JPAB	1999173431	0	<u>L4</u>
JPAB	2001059191	1	<u>L3</u>
JPAB	173431	0	<u>L2</u>
USPT,JPAB	173431	16	<u>L1</u>

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